

**Silicon PNP transistor triple diffused type
AP845**

[Applications]

High voltage switching
High voltage driver

[Feature]

High collector breakdown voltage VCEO= -400V, VCBO= -400V

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-400	V
Collector-emitter voltage	VCEO	-400	V
Emitter-base voltage	VEBO	-7	V
Collector current (DC)	IC	-0.5	A
Collector current (Pulse)	ICP	-1	A
Base current	IB	-0.25	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BVCEO	-400	-	-	V	IC= -10mA, IB= 0A
Collector cut-off current	ICBO	-	-	-10	uA	VCB= -400V, IE= 0A
Emitter cut-off current	IEBO	-	-	-1	uA	VEB= -7V, IC= 0A
DC current gain 1	hFE1	140	-	450	-	VCE= -5V, IC= -20mA
DC current gain 2	hFE2	140	-	400	-	VCE= -5V, IC= -0.1A
Collector-emitter saturation voltage	VCE(sat)	-	-	-1	V	IC= -0.1A, IB= -10mA
Base-emitter saturation voltage	VBE(sat)	-	-	-0.9	V	IC= -0.1A, IB= -10mA
Transition frequency	fT	-	35	-	MHz	VCE= -5V, IE= 50mA
Collector output capacitance	Cob	-	18	-	pF	VCB= -10V, IE= 0A, f= 1MHz
Rise time	tr	-	0.2	-	us	VCC= -200V, IC= -0.1A
Storage time	tstg	-	2.3	-	us	IB1= -10mA, IB2= 20mA
Fall time	tf	-	0.2	-	us	Duty cycle<= 1%

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

